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L Number	Hits	Search Text	DB	Time stamp
-	1366860	semiconductor	USPAT;	2004/05/03 15:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3311	hydrogen near2 anneal\$4	USPAT;	2004/05/03 15:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	(hydrogen near2 anneal\$4) with sublim\$5	USPAT;	2004/05/03 15:21
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		l	IBM_TDB	
-	52	(hydrogen near2 anneal\$4) and sublim\$5	USPAT;	2004/05/03 15:22
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
[]	_	(h) draman nam? (/h aak a di kaa akaa aak) aa aa aa ah di)	IBM_TDB	0004/05/00 40:00
-	2	(hydrogen near2 ((heat adj treatment) or anneal\$4)) with	USPAT;	2004/05/03 16:00
		sublim\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	79	(hydrogen near2 ((heat adj treatment) or anneal\$4)) and	IBM_TDB USPAT;	2004/05/03 15:26
-	19	sublim\$5	US-PGPUB;	2004/03/03 13.20
		- oubmitwo	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	4	(hydrogen near2 anneal\$4) same sublim\$5	USPAT;	2004/05/03 15:24
	•	1 () = 1 - 3 - 1	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2580	(hydrogen near2 ((heat adj treatment) or anneal\$4)) and	USPAT;	2004/05/03 15:41
		(insulat\$4 or (silicon adj dioxide))	US-PGPUB;	
			EPO; JPO;	
,			DERWENT;	
			IBM_TDB	
-	71	[(() 3 (())	USPAT;	2004/05/03 15:47
		(insulat\$4 or (silicon adj dioxide))) and (((first or upper) adj	US-PGPUB;	
		side) with substrate)	EPO; JPO;	
			DERWENT;	
	46	(/hydrogon noor) (/host adi trastment)	IBM_TDB	0004/05/00 45:40
-	16	((hydrogen near2 ((heat adj treatment) or anneal\$4)) and	USPAT;	2004/05/03 15:49
		(insulat\$4 or (silicon adj dioxide))) and (((first or upper) adj	US-PGPUB;	
		side) with substrate) and ((((second or buttom) adj side) or underside) with substrate)	EPO; JPO;	
		underside) with substrate)	DERWENT; IBM_TDB	
_	6168	 semiconductor and sublim\$5	USPAT;	2004/05/03 15:51
	0100	Semiconductor and subilities	US-PGPUB;	2007/00/03 13.31
			EPO; JPO;	
[DERWENT;	
			IBM_TDB	
-	12206	semiconductor and (insulat\$4 with (first or upper) with	USPAT;	2004/05/03 15:58
		(second or buttom) with side)	US-PGPUB;	
]		,	EPO; JPO;	
			DERWENT:	
			IBM_TDB	
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-	7601	semiconductor and (substrate same (insulat\$4 with (first or	USPAT;	2004/05/03 15:59
		upper) with (second or buttom) with side))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	91	(semiconductor and (substrate same (insulat\$4 with (first or	USPAT;	2004/05/03 16:01
		upper) with (second or buttom) with side))) and (hydrogen	US-PGPUB;	
		near2 ((heat adj treatment) or anneal\$4))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	14	((semiconductor and (substrate same (insulat\$4 with (first or	USPAT;	2004/05/03 16:03
		upper) with (second or buttom) with side))) and (hydrogen	US-PGPUB;	
		near2 ((heat adj treatment) or anneal\$4))) and (etch\$4 with	EPO; JPO;	
		insulat\$5 with (first or upper) with substrate)	DERWENT;	
			IBM_TDB	